

## **BUK9607-30B**

# N-channel TrenchMOS logic level FET Rev. 02 — 31 January 2011

Product data sheet

#### 1. **Product profile**

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

### 1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u> .	-	-	75	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see Figure 2		-	-	157	W
Static cha	racteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V; } I_D = 25 \text{ A;}$ $T_j = 25 \text{ °C}$		-	4.4	5	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{see Figure 12}};$		-	5.9	7	mΩ



### N-channel TrenchMOS logic level FET

Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 75 \text{ A}; V_{sup} \le 30 \text{ V};$ $R_{GS} = 50 \Omega; V_{GS} = 5 \text{ V};$ $T_{j(init)} = 25 \text{ °C}; unclamped$	-	-	327	mJ
Dynamic cl	naracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 24 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 13</u>	-	7.6	-	nC

<sup>[1]</sup> Continuous current is limited by package.

### 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
3	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

<sup>[1]</sup> It is not possible to make a connection to pin 2 of the SOT404 package.

### 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9607-30B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

### 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
				141111		
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	30	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	30	V
$V_{GS}$	gate-source voltage			-15	15	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 5 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u>	-	108	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; see <u>Figure 1</u>	[1]	-	75	Α
		$T_{mb}$ = 25 °C; $V_{GS}$ = 5 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	[2]	-	75	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; see Figure 3		-	435	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	157	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
Is	source current	T <sub>mb</sub> = 25 °C	[1]	-	108	Α
			[2]	-	75	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	435	Α
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 75 A; $V_{sup} \le 30$ V; $R_{GS}$ = 50 $\Omega$ ; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	327	mJ

<sup>[1]</sup> Current is limited by power dissipation chip rating.

<sup>[2]</sup> Continuous current is limited by package.

### N-channel TrenchMOS logic level FET

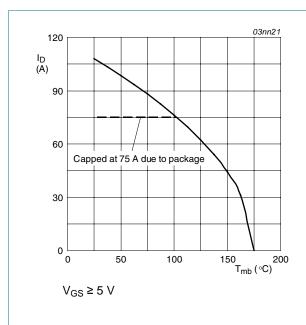


Fig 1. Normalized total power dissipation as a function of mounting base temperature

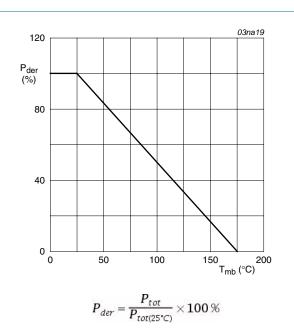
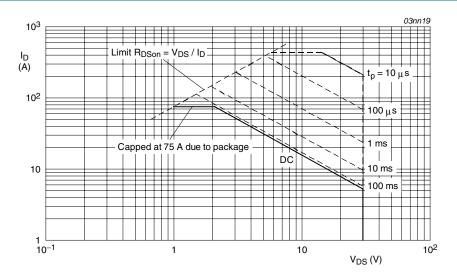


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25^{\circ}C; I_{DM}$  is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.95	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

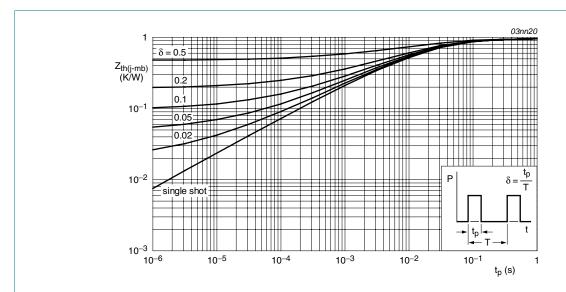


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
•	aracteristics	Conditions		ijΡ	Mux	Oilit
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = 25 \text{ °C}$	30	_	_	V
- (DK)USS	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = -55 \text{ °C}$	27	-	-	
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_i = 25 \text{ °C};$	1.1	1.5	2	
00(11)	g	see Figure 10				
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see <u>Figure 10</u>	0.5	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 10	-	-	2.3	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 ^{\circ}\text{C}$	-	-	500	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 15 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	V μΑ
		$V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	4.4	5	mΩ
	resistance	$V_{GS} = 5 \text{ V; } I_D = 25 \text{ A; } T_j = 175 \text{ °C;}$ see Figure 11; see Figure 12	-	-	13.3	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	-	9	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 11; see Figure 12	-	5.9	7	mΩ
Dynamic	characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{}$	-	32	-	nC
$Q_{GS}$	gate-source charge		-	13	-	nC
$Q_{GD}$	gate-drain charge		-	7.6	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	2530	3373	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	635	762	pF
C <sub>rss</sub>	reverse transfer capacitance		-	268	367	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 25 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	30	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 ^{\circ}C$	-	135	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	99	-	ns
t <sub>f</sub>	fall time		-	98	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25$ °C	-	2.5	-	nΗ
		from drain lead 6 mm from package to centre of die ; $T_j = 25$ °C	-	4.5	-	nΗ
L <sub>S</sub>	internal source inductance	from source lead 6 mm from package to source bond pad ; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nΗ
Source-d	rain diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 15</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	52	-	ns
Qr	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	35	-	nC

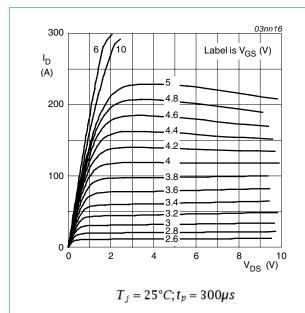


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

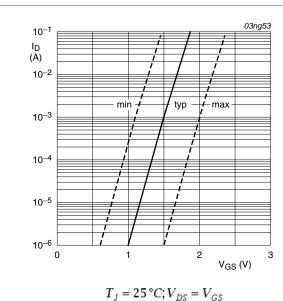


Fig 7. Sub-threshold drain current as a function of gate-source voltage

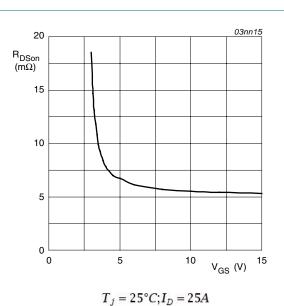


Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

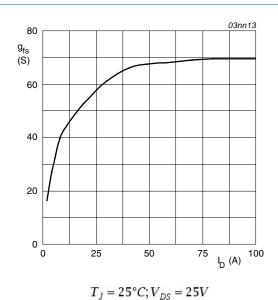


Fig 8. Forward transconductance as a function of drain current; typical values

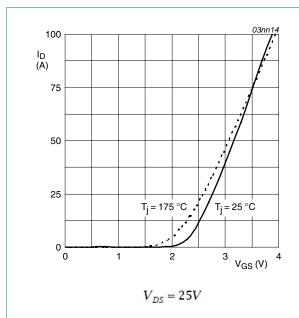


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

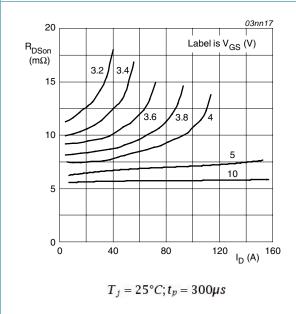
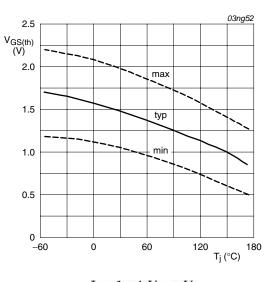


Fig 11. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 1mA; V_{DS} = V_{GS}$ 

Fig 10. Gate-source threshold voltage as a function of junction temperature

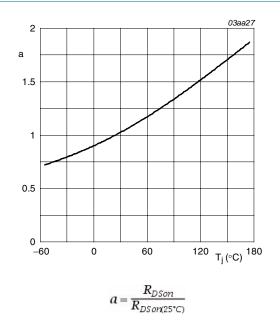


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

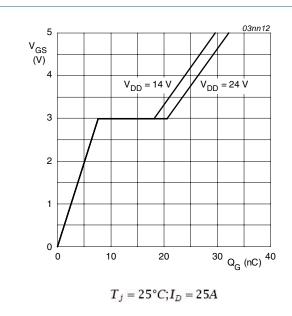
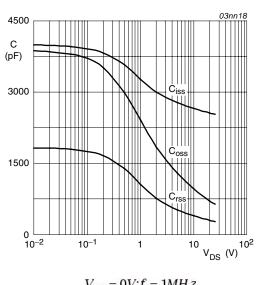
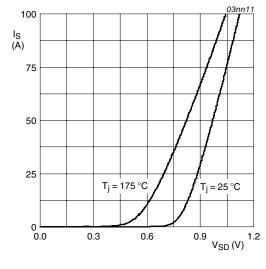


Fig 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $V_{GS} = 0V$ 

Fig 15. Source current as a function of source-drain voltage; typical values

### 7. Package outline

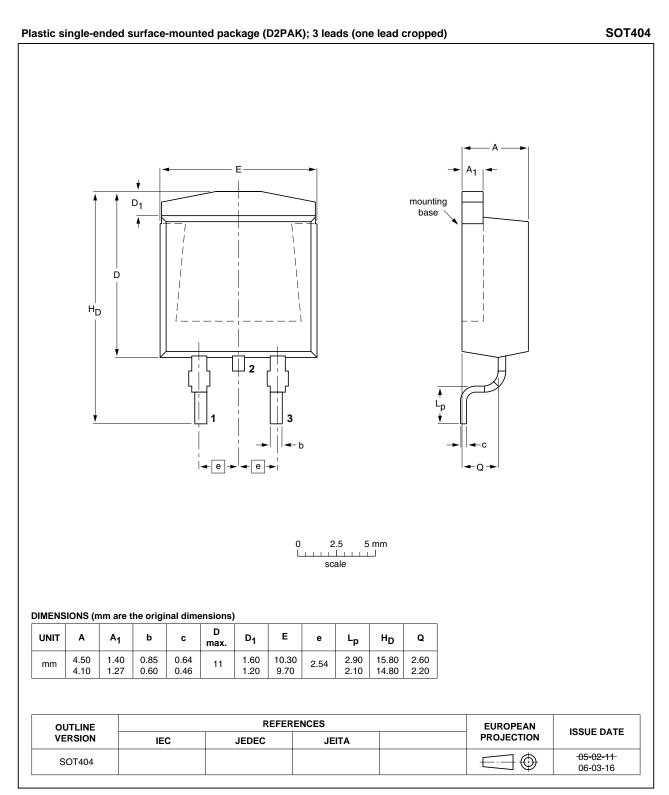


Fig 16. Package outline SOT404 (D2PAK)

N-channel TrenchMOS logic level FET

### 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BUK9607-30B v.2	20110131	Product data sheet	-	BUK95_9607_30B v.1		
Modifications:	<ul> <li>The format of this of NXP Semicondu</li> </ul>	mat of this data sheet has been redesigned to comply with the new identity guide Semiconductors.				
	<ul> <li>Legal texts have be</li> </ul>	een adapted to the new c	ompany name where app	oropriate.		
	<ul> <li>Type number BUK</li> </ul>	9607-30B separated from	data sheet BUK95_960	7_30B v.1.		
BUK95_9607_30B v.1	20030425	Product data	-	-		

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#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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### BUK9607-30B

### **Nexperia**

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